

ABSTRACT

A plasma etching method includes a physisorption step for causing an adsorbate that is based on first processing gas to be physisorbed onto a film to be etched, while
5 cooling an object to be processed on which the film to be etched is provided; and an etching step for etching the film to be etched by causing the adsorbate to react with the film to be etched, using the plasma of second processing gas.